## PdSe2 Single Crystals Synthesized by Flux Method

Vera Marinova<sup>1\*</sup>, Nikolay Minev<sup>1</sup>, Bogdan Ranguelov<sup>2</sup>, Valentina Mussi<sup>3</sup>, Walter Fuscaldo<sup>3</sup>, Dimitrios Zografopoulos<sup>3</sup>, and Dimitre Dimitrov<sup>1,2</sup>
\*vmarinova@iomt.bas.bg

PdSe2 possesses a low-symmetry pentagonal, layered structure. With unique atomic arrangement leads to interesting mechanical properties, including unusual negative Poisson's ratio and ultra-high mechanical strength [1]. Furthermore, this low-symmetry structure offers new characteristics for in-plane anisotropy in optics and electronics. For example, PdSe<sub>2</sub> possesses a strong linear dichroism ratio, up to 1.9, which can act as a high polarizationsensitive photodetector [2]. Notably, both chemical vapor deposition (CVD) grown and exfoliated PdSe2 exhibit extremely high air quality stability and device performance stability, which provides an excellent opportunity for future large-scale electronic device applications. Palladium diselenide (PdSe2), a noble metal dichalcogenide, has emerged as a new 2D material with widely tunable bandgap for device applications, however the direct synthesis of highquality PdSe2 is still challenging. Here we demonstrate the growth process of single-crystal PdSe<sub>2</sub>. The PdSe<sub>2</sub> single crystal was synthesized by a self-flux (high-temperature solution) method using Se as a fluxing agent. Selenium with a purity of 99.999% was used as a solvent and a preliminary solid-phase synthesis of the compound PdSe<sub>2</sub> was carried, using Pd and Se in stoichiometric amounts as starting materials. To carry out the crystal growth process, the synthesized material was placed in quartz ampoules pumped to a vacuum of 10-5 torr. The growth process was carried out for 4 days at 850°C. Under these conditions, crystals with sizes of 2-3 cm<sup>3</sup> were obtained and crystal quality characterized by XRS, XPS and Raman spectroscopy.

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## References:

[1] Lei, W.; Cai, B.; Zhou, H.; Heymann, G.; Tang, X.; Zhang, S.; Ming, X. Ferroelastic lattice rotation and band-gap engineering in quasi 2D layered-structure PdSe2 under uniaxial stress. Nanoscale 2019, 11, 12317–1232 [2] Zhang, G.; Amani, M.; Chaturvedi, A.; Tan, C.; Bullock, J.; Song, X.; Kim, H.; Lien, D.-H.; Scott, M.C.; Zhang, H.; et al. Optical and electrical properties of two-dimensional palladium diselenide. Appl. Phys. Lett. 2019, 114, 253102

<sup>&</sup>lt;sup>1</sup> Institute of Optical Materials and Technologies, Bulgarian Academy of Sciences, 1113 Sofia, Bulgaria

<sup>&</sup>lt;sup>2</sup>Institute of Physical Chemistry, Bulgarian Academy of Sciences, 1113 Sofia, Bulgaria

<sup>&</sup>lt;sup>3</sup>Consiglio Nazionale delle Ricerche, Istituto per la Microelettronica e Microsistemi, 00133 Rome, Italy

<sup>&</sup>lt;sup>4</sup>Institute of Solid State Physics, Bulgarian Academy of Sciences, 1784 Sofia, Bulgaria